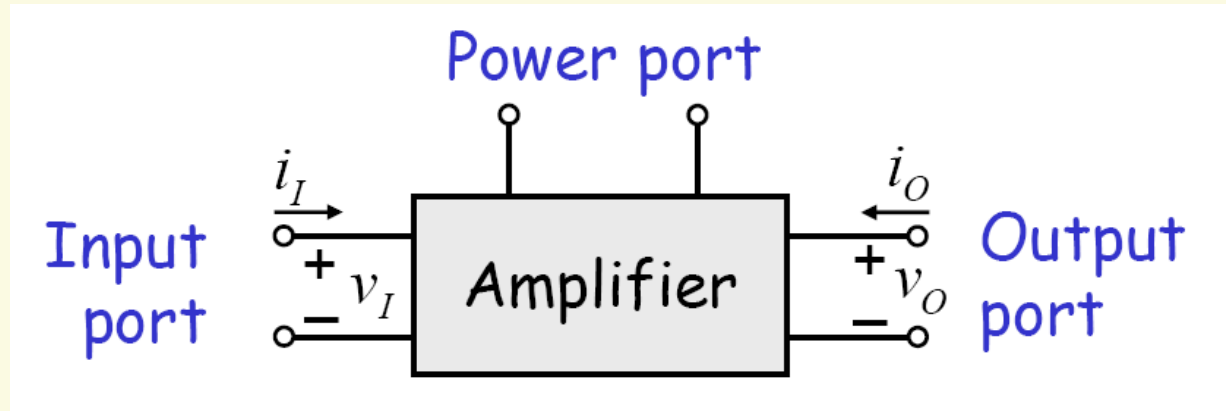



Chap. 7 The MOSFET Amplifier

Signal Amplification
Actual MOSFET Characteristics
MOSFET Amplifier
Large Signal Analysis
Bipolar Junction Transistor (BJT)

Signal Amplification

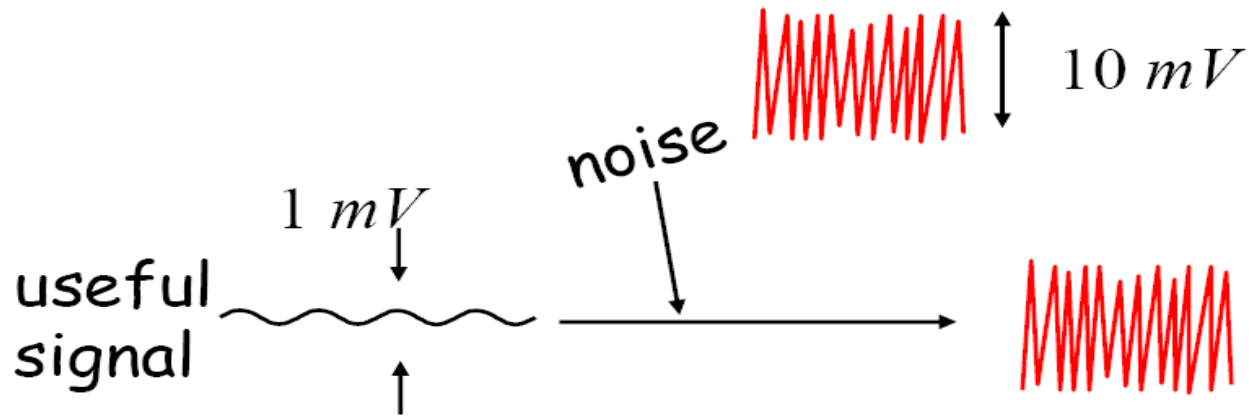


 **Amplifier: power gain**

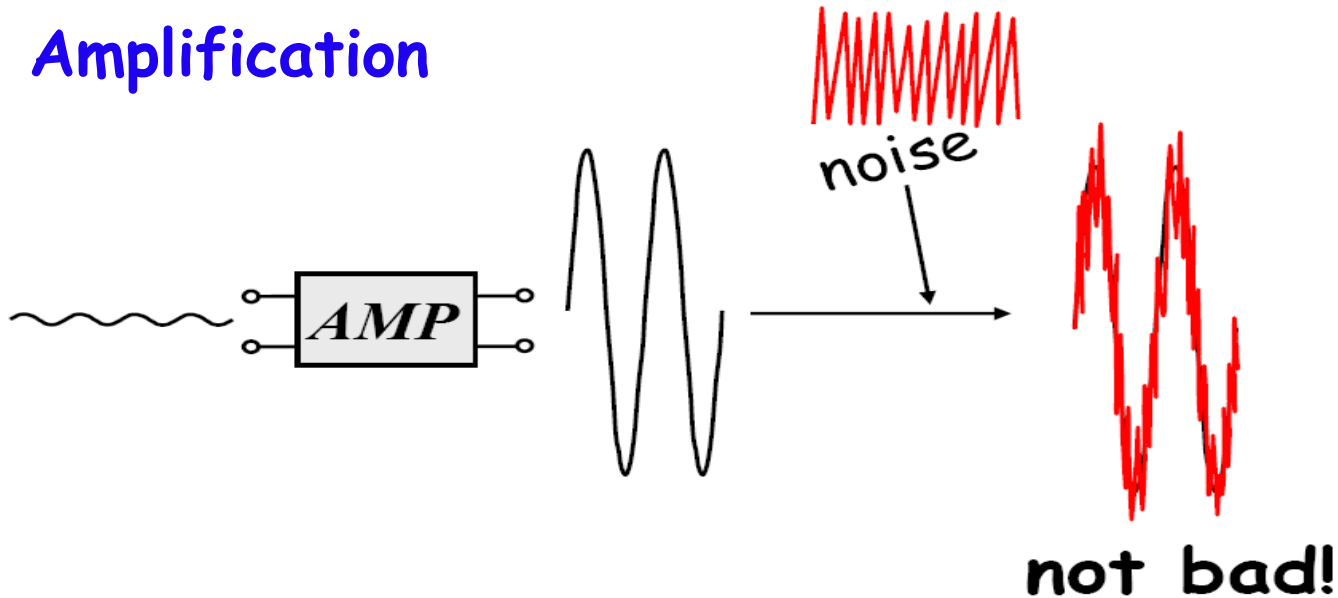
- noise tolerance
- buffering

Why Amplify? (Analog)

No amplification

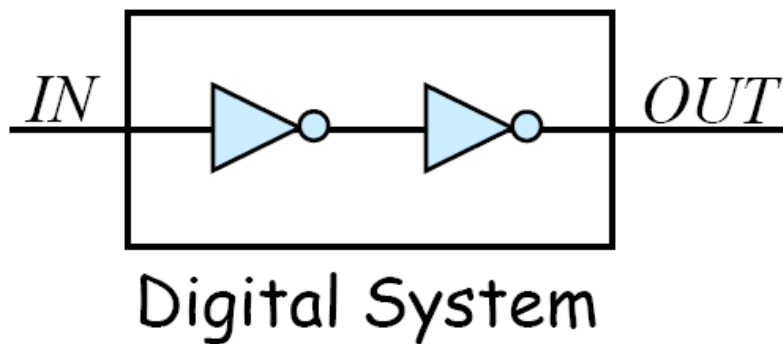
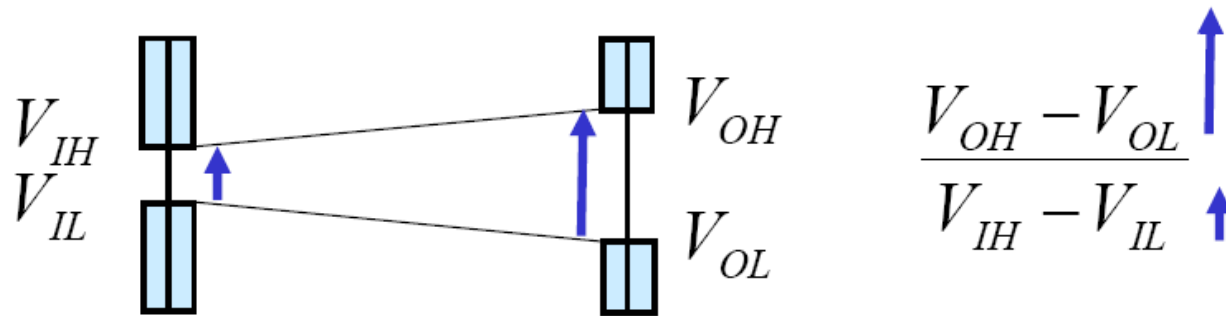


Amplification

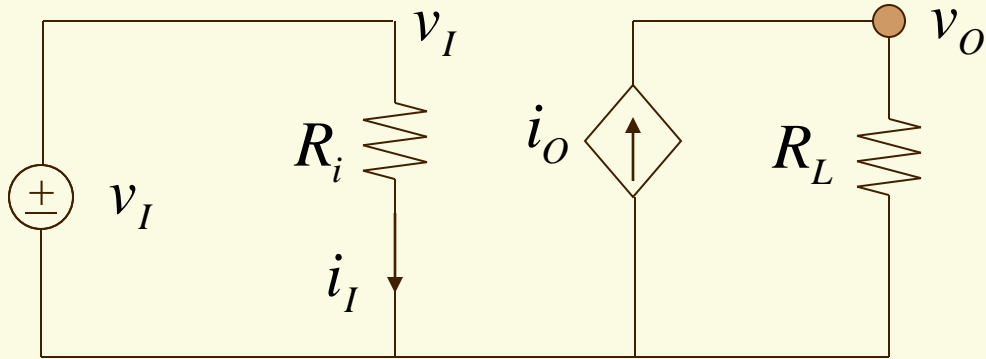


Why amplify? (Digital)

Static discipline requires amplification!
Minimum amplification needed:



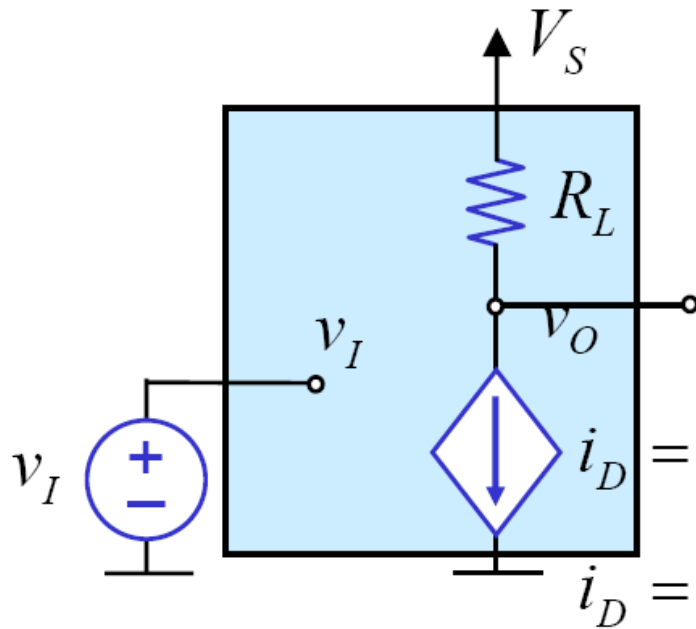
VCCS Circuit: Linear Amplifier



$$i_o = f(v_I) = -g_m v_I$$

$$\frac{v_o}{v_I} ? \quad \frac{i_o}{i_I} ? \quad \frac{P_o}{P_I} ?$$

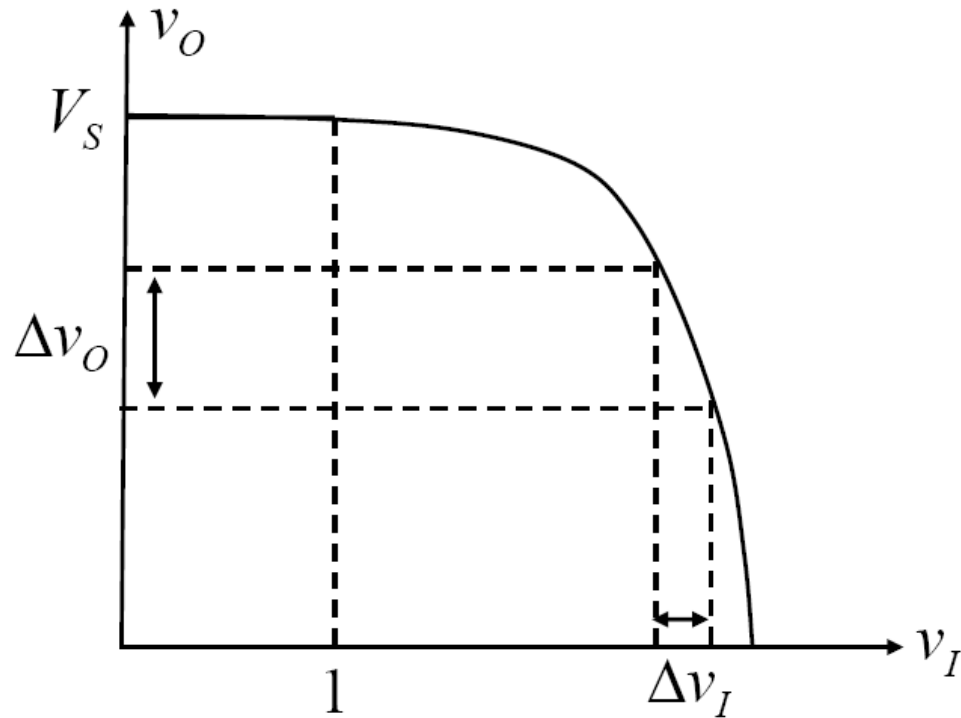
Example



$$V_S = 10V, \quad K = 2 \frac{mA}{V^2}, \quad R_L = 5k\Omega$$

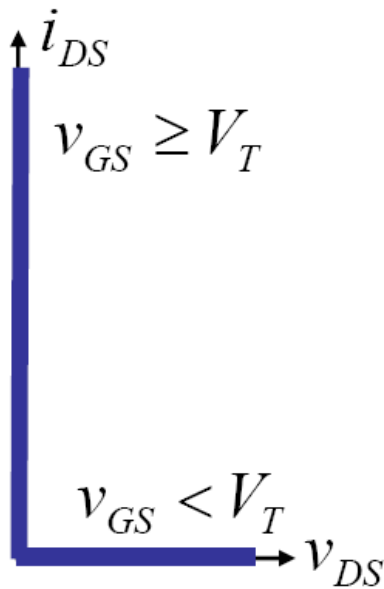
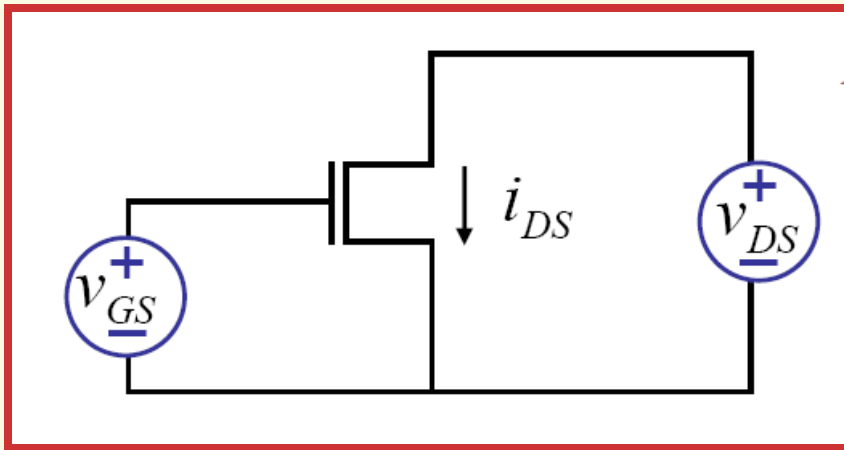
$$i_D = \frac{K}{2}(v_{IN} - 1)^2 \quad \text{for } v_{IN} \geq 1$$
$$i_D = 0 \quad \text{otherwise}$$

Example – cont'd

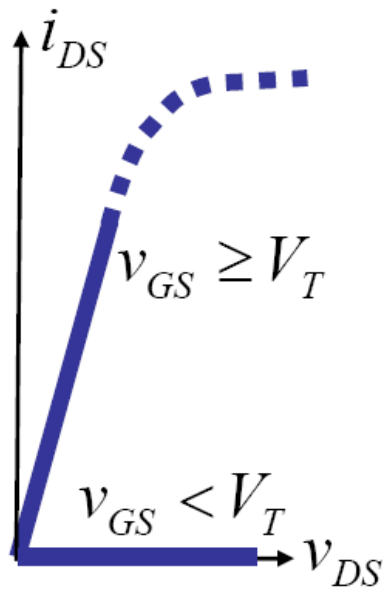


$$\frac{\Delta v_O}{\Delta v_I} > 1 \quad \longrightarrow \quad \text{amplification}$$

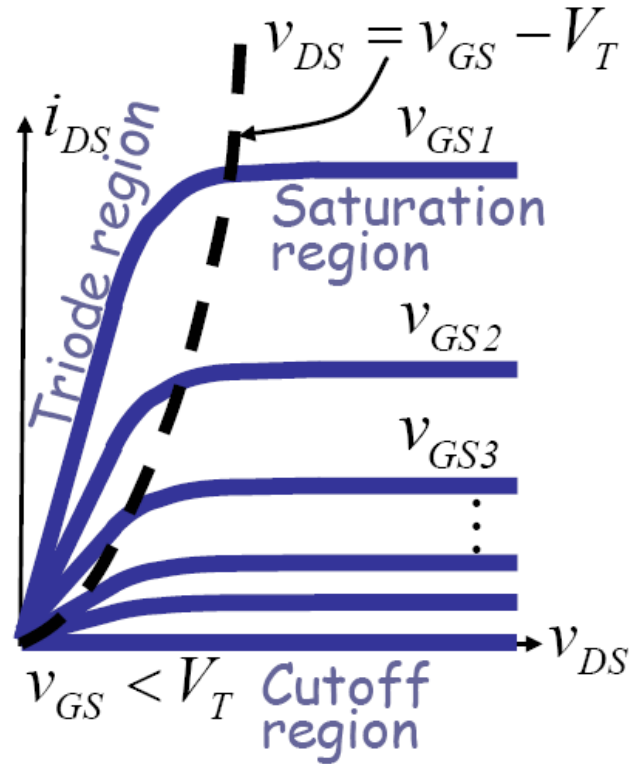
Actual MOSFET Characteristics



S MODEL

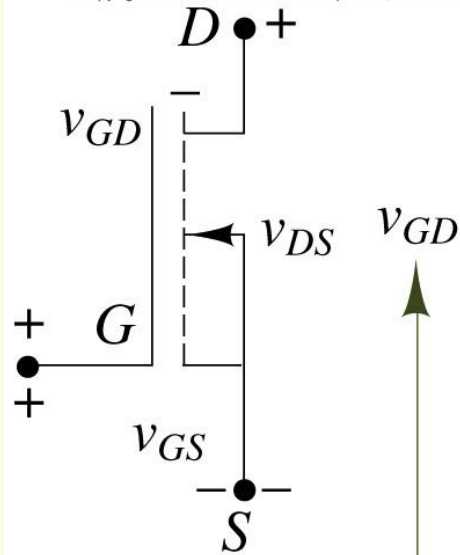


SR MODEL



Remind: Region of Operation of NMOS

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**Region 3:
Triode**

$$V_{GS} \geq V_T, \quad V_{GD} \geq V_T$$

$$i_D = K[2(V_{GS} - V_T)V_{DS} - V_{DS}^2]$$

**Region 2:
Saturation**

$$V_{GS} \geq V_T, \quad V_{GD} < V_T$$

$$i_D = K(V_{GS} - V_T)^2 \left(1 + \frac{V_{DS}}{V_A}\right)$$

$$\approx K(V_{GS} - V_T)^2$$

**Region 1:
Cutoff**

$$V_{GS} < V_T, \quad V_{GD} < V_T$$

$$i_D = 0$$

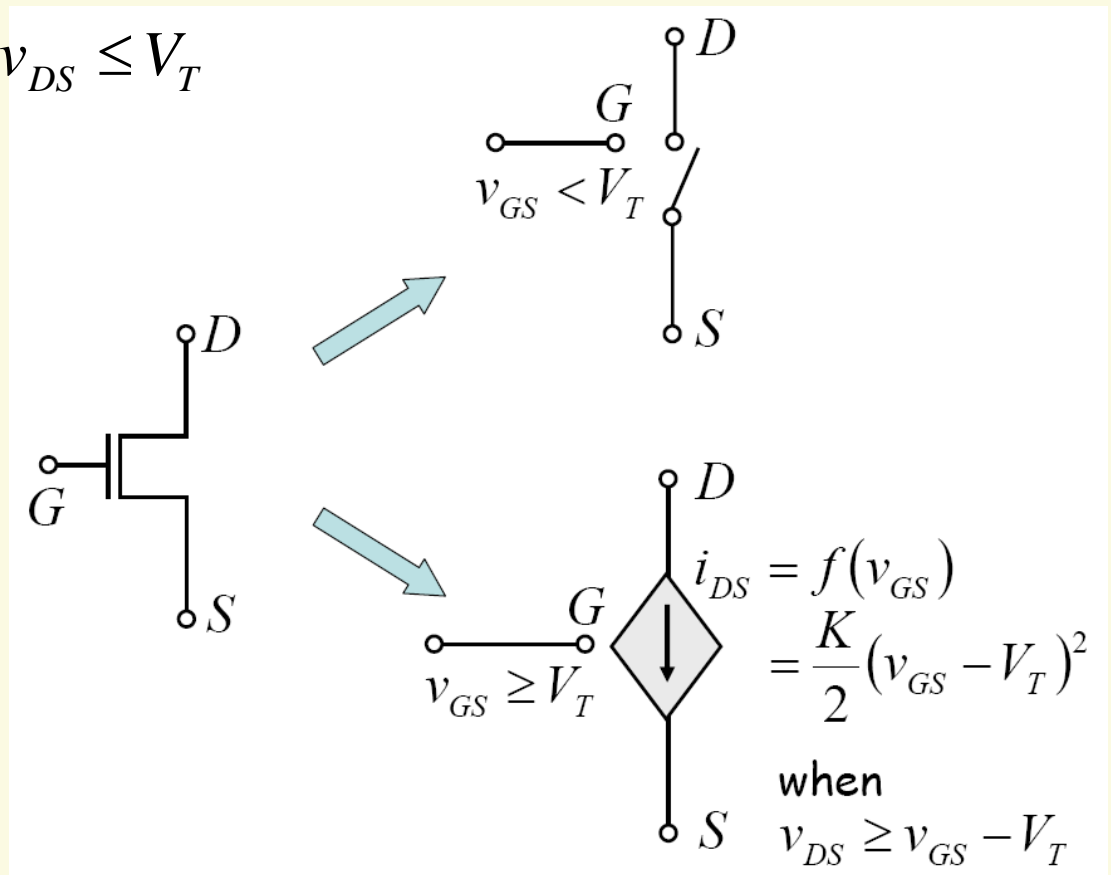
MOSFET SCS Model

SCS Model: Switched Current Source Model

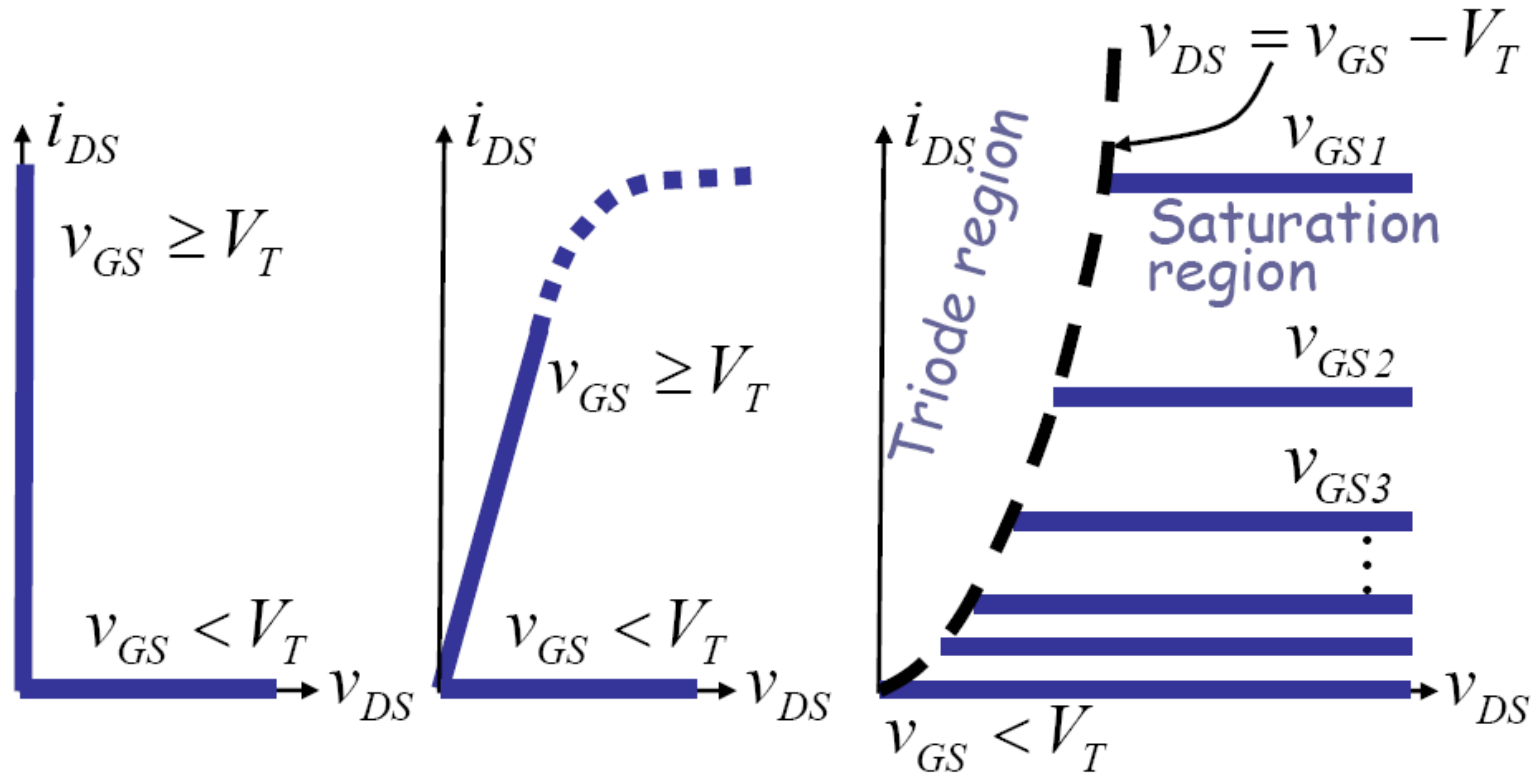
- Saturation region of operation: “saturation principle”

$$v_{GS} \geq V_T, \quad v_{GD} = v_{GS} - v_{DS} \leq V_T$$

$$i_{DS} = \frac{1}{2} K (v_{GS} - V_T)^2$$



Reconciling the Models



S MODEL

for fun!

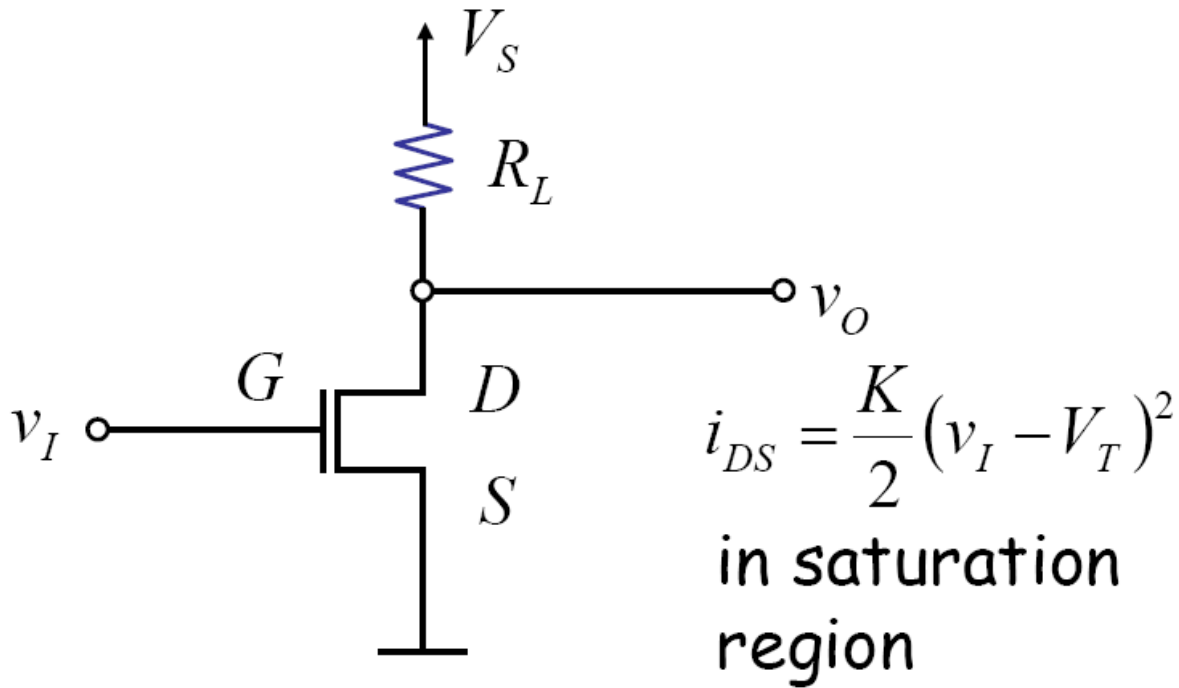
SR MODEL

for digital
designs

SCS MODEL

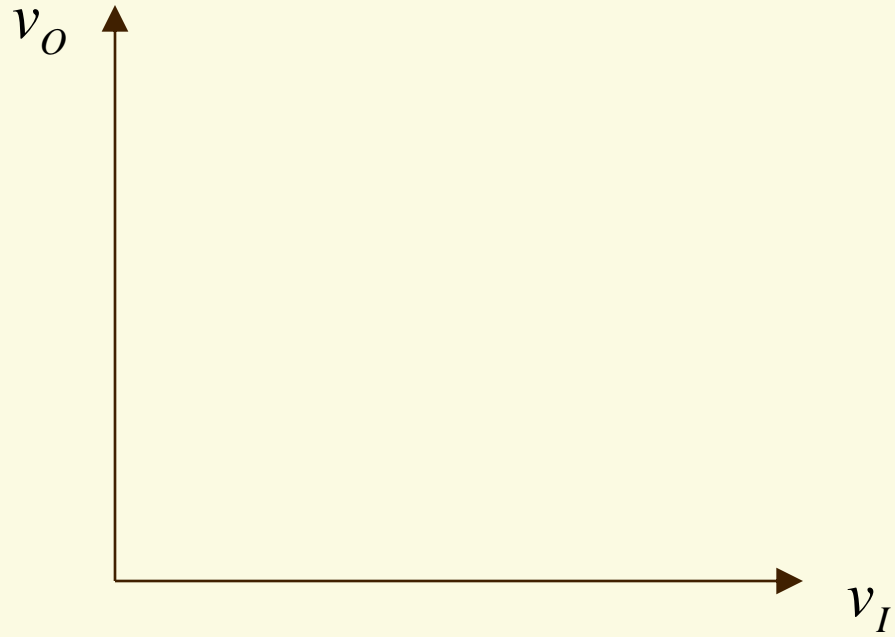
for analog
designs

MOSFET Amplifier

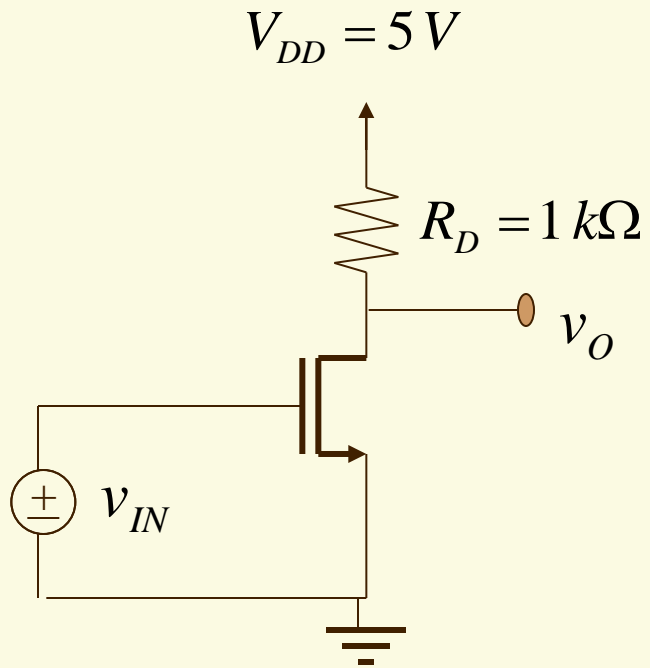


📄 What is the voltage gain?

Voltage Characteristics

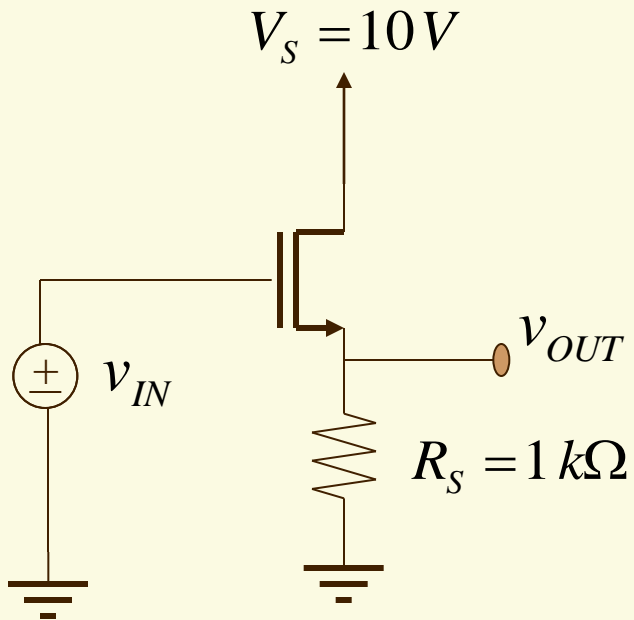


Example 7.7



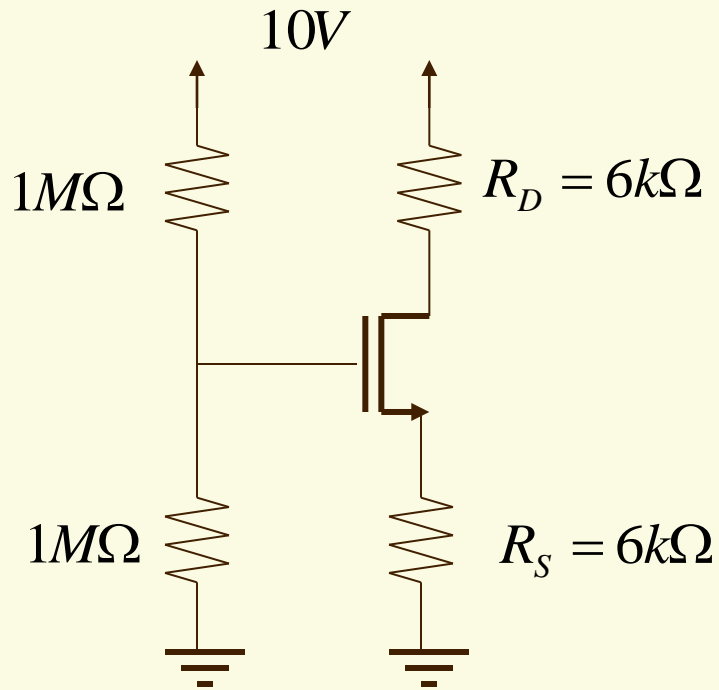
$$V_T = 0.8\text{ V}, K = 0.5\text{ mA/V}^2$$

Example 7.8: Source Follower Circuit



$$V_T = 1\text{ V}, K = 2\text{ mA/V}^2$$

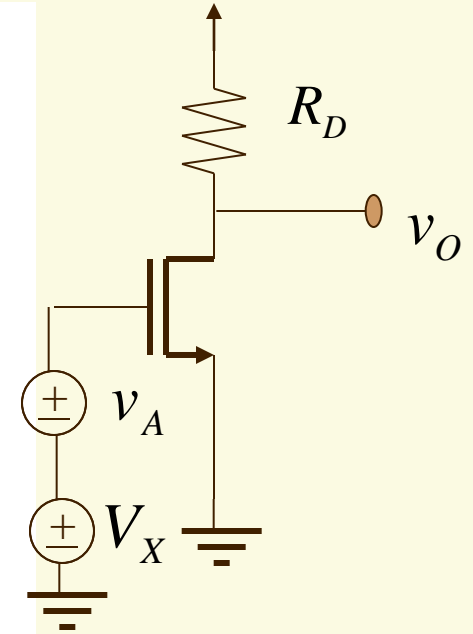
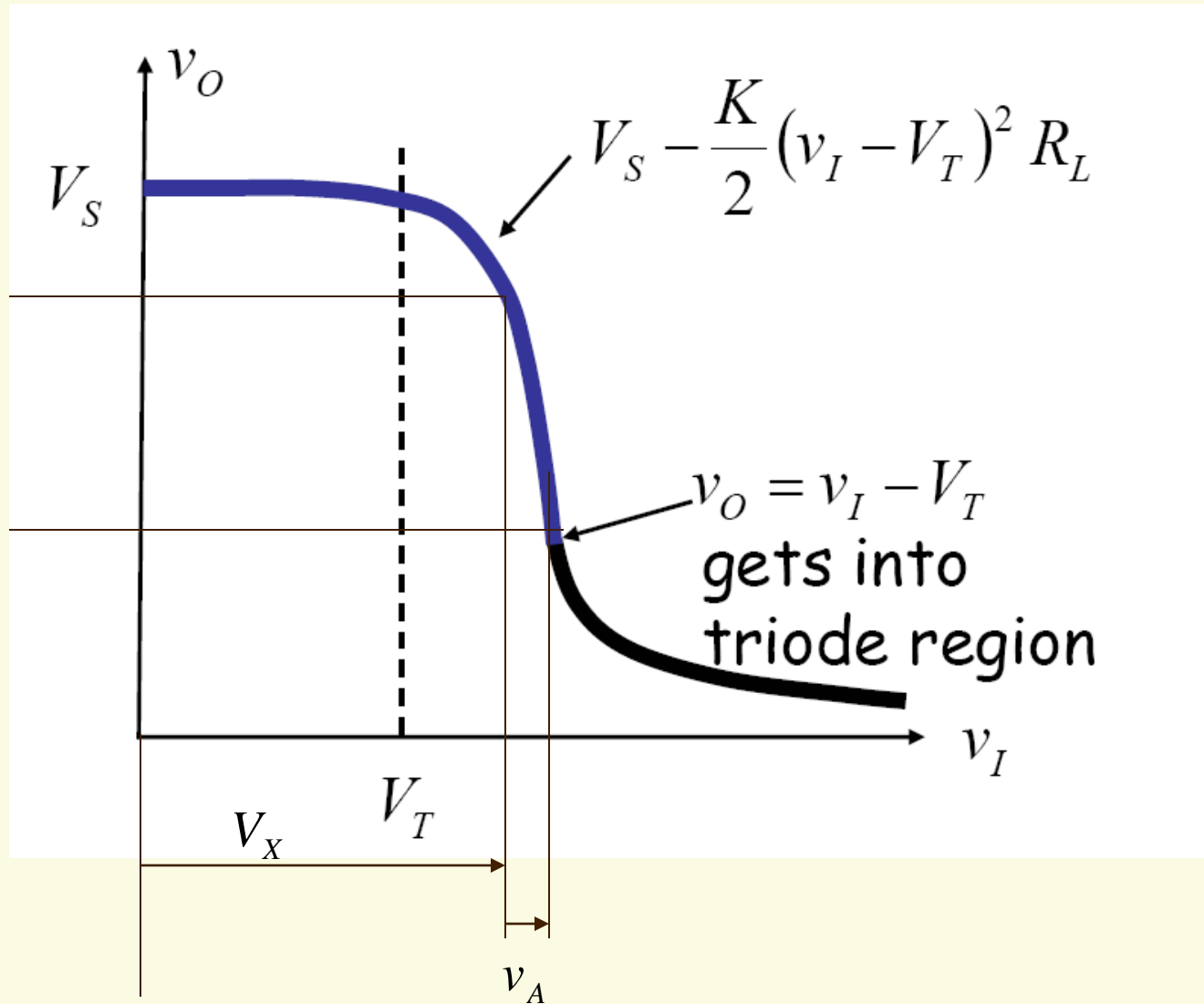
Exercise



$$V_T = 1.0V, K = 0.5mA/V$$

$$i_D \quad ?$$

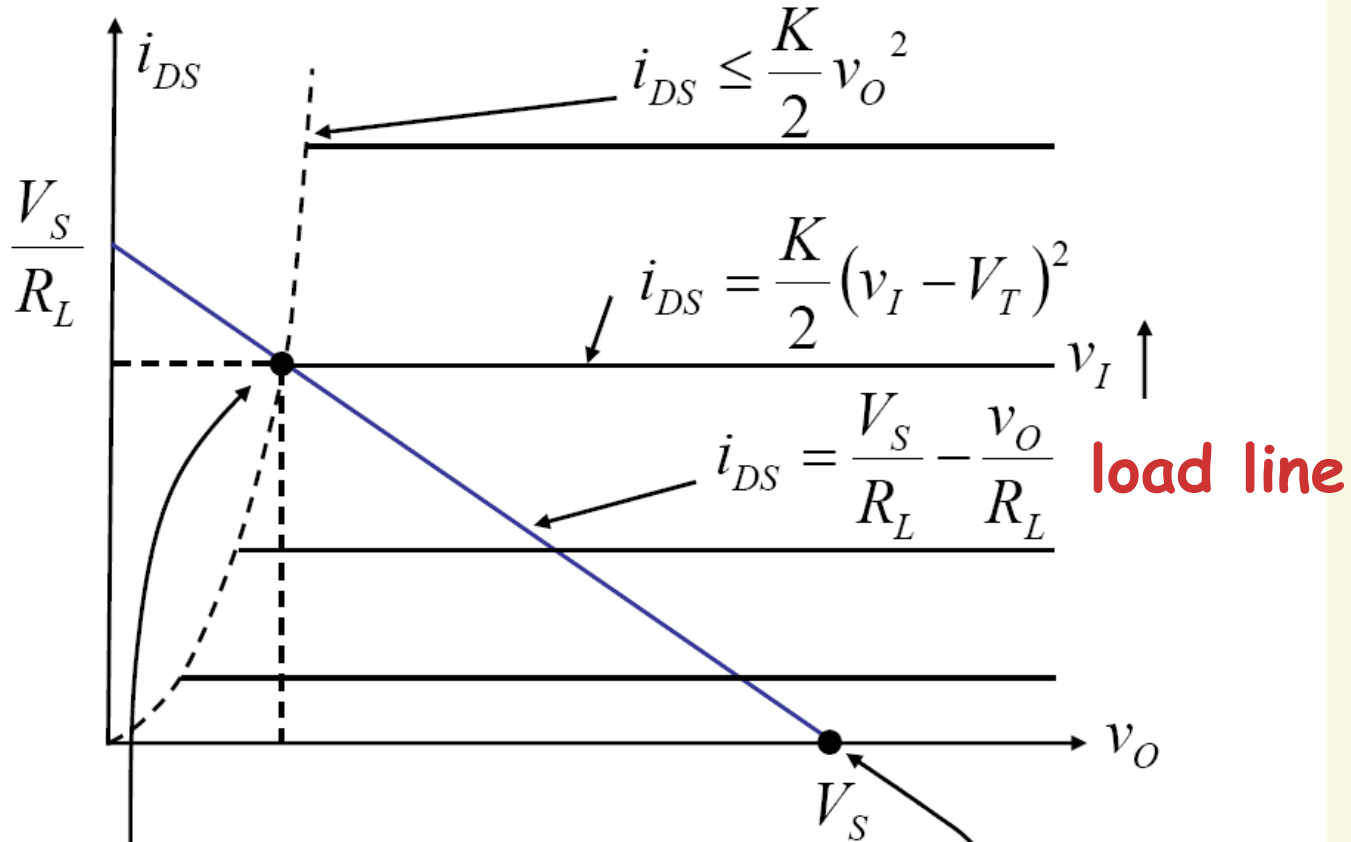
Biasing the Circuit



Large Signal Analysis

- Relationship between v_O and v_{IN}
- What is the range of valid input values under the saturation discipline? What is the corresponding range of output values?

Graphical Analysis



$v_I = V_T$
 $v_O = V_S$ and $i_{DS} = 0$

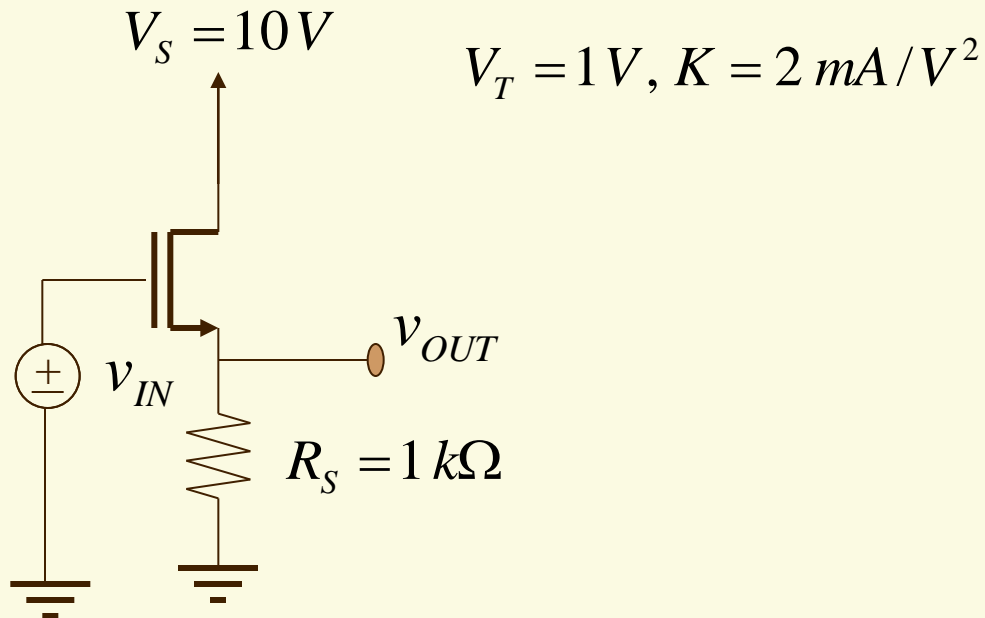
$$v_I = V_T + \frac{-1 + \sqrt{1 + 2KR_L V_S}}{KR_L}$$

$$v_O = \frac{-1 + \sqrt{1 + 2KR_L V_S}}{KR_L}$$

$$i_{DS} = \frac{V_S}{R_L} - \frac{v_O}{R_L}$$

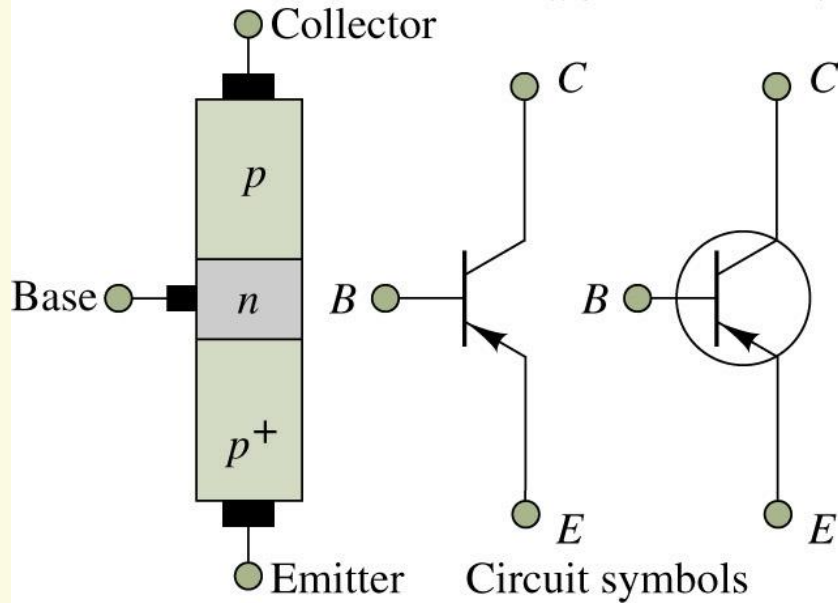
Example 7.10, 7.11

- Valid ranges for the source follower circuit.
- Operating point for maximum input swing

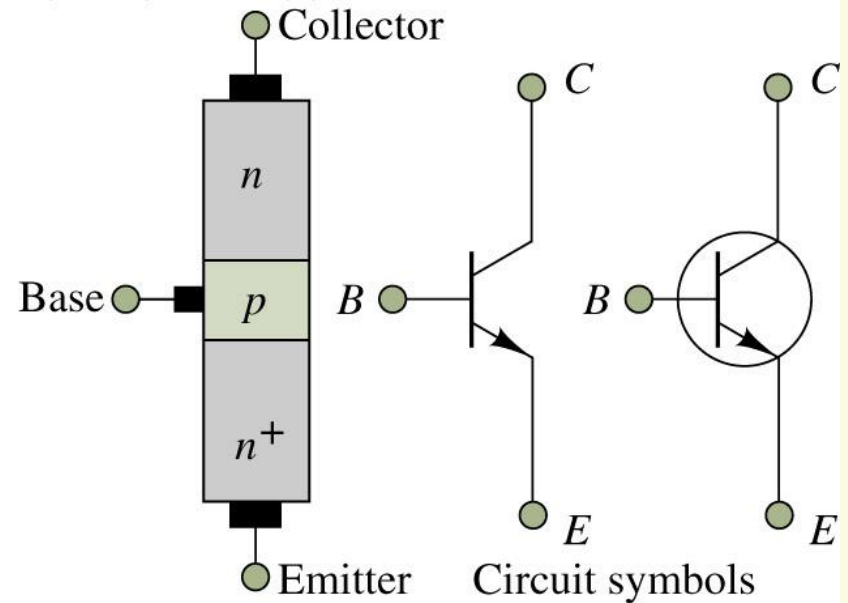


Bipolar junction transistors

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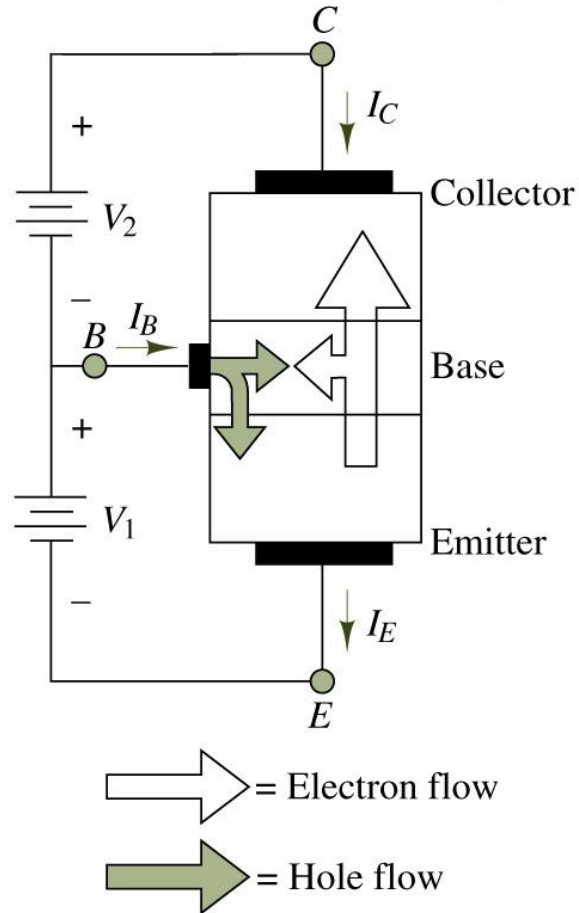
pnp transistor



npn transistor

Operation Principle

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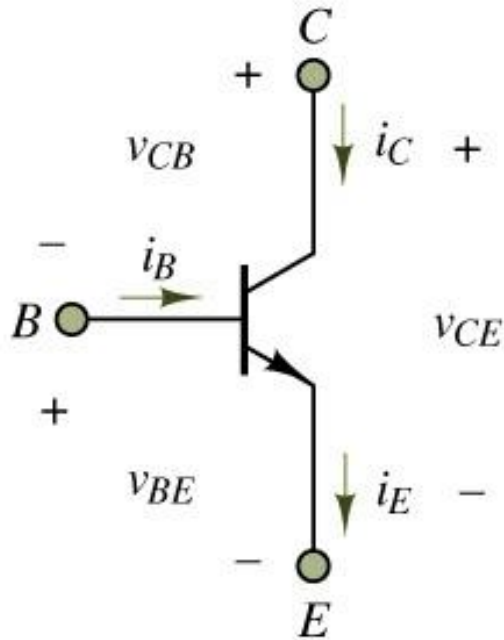


When the BC junction is reverse-biased, the electrons from the emitter region are swept across the base into the collector.

Definition of BJT voltages and currents

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The operation of the BJT is defined in terms of two currents and two voltages: i_B , i_C , v_{CE} , and v_{BE} .



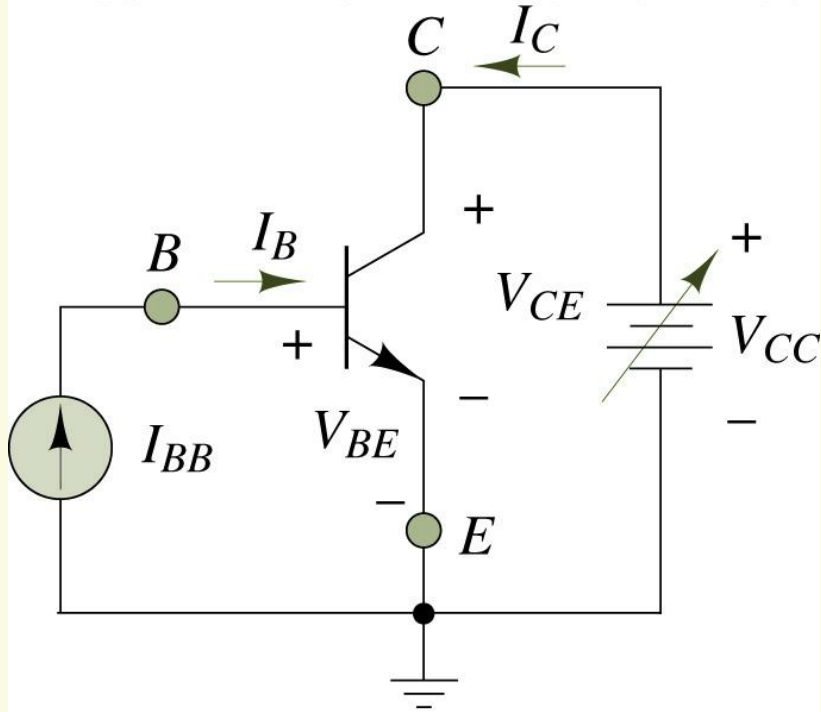
$$\text{KCL: } i_E = i_B + i_C$$

$$\text{KVL: } v_{CE} = v_{CB} + v_{BE}$$

$$I_C = \beta I_B, \quad I_C = \alpha I_E, \quad I_E = I_C + I_B$$

Ideal test circuit to determine the i-v characteristic

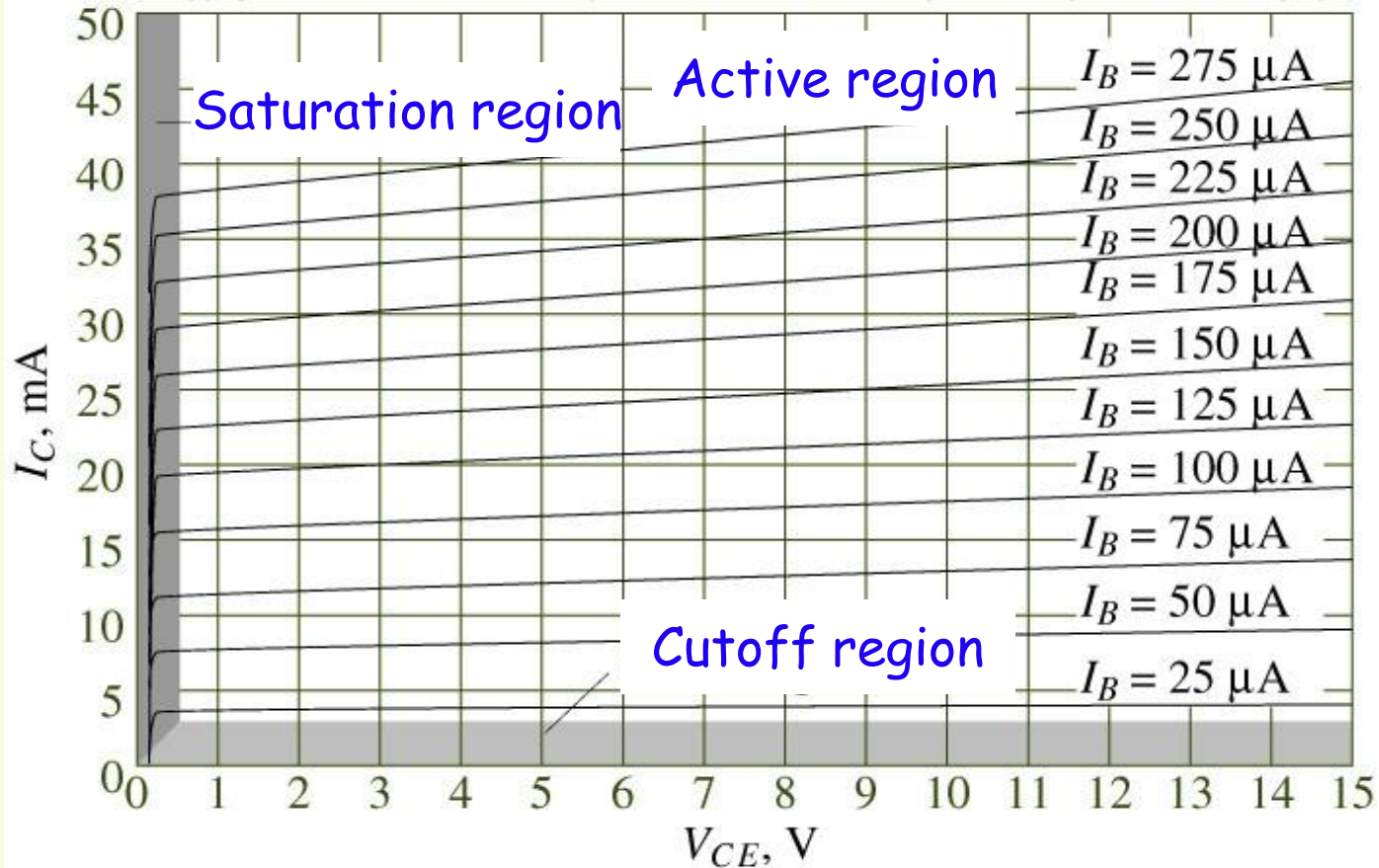
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(a)

Collector-Emitter Output Characteristics

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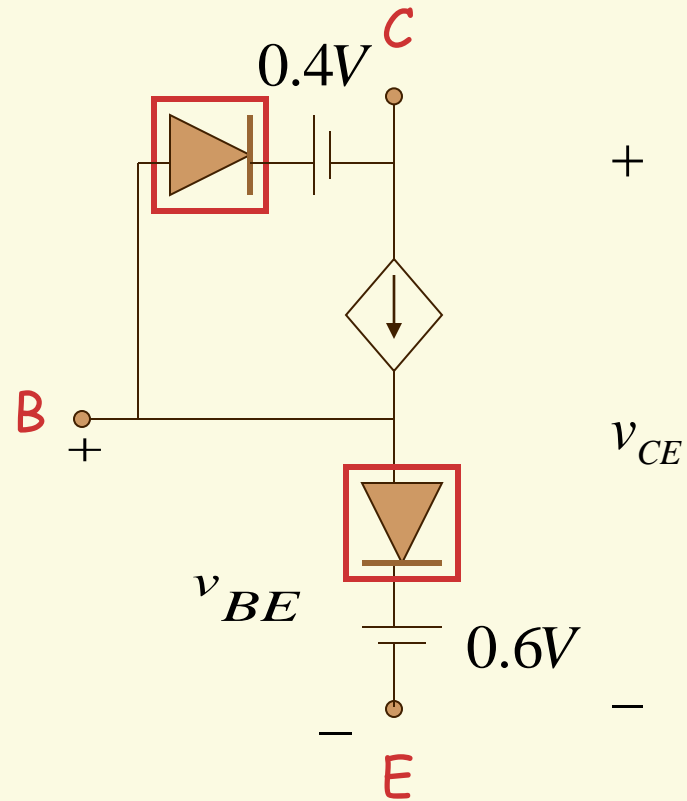
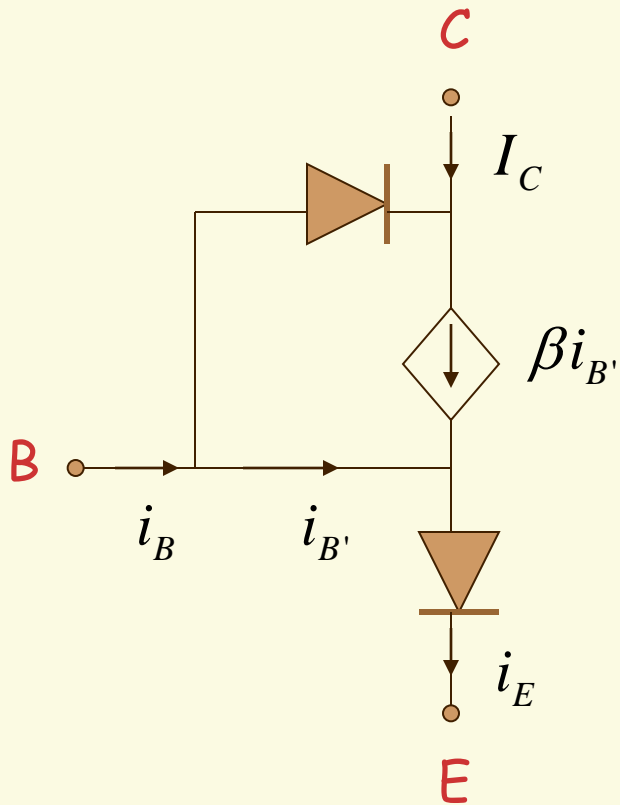


Breakdown region

Saturation region: $V_{CE} < 0.2$, almost constant

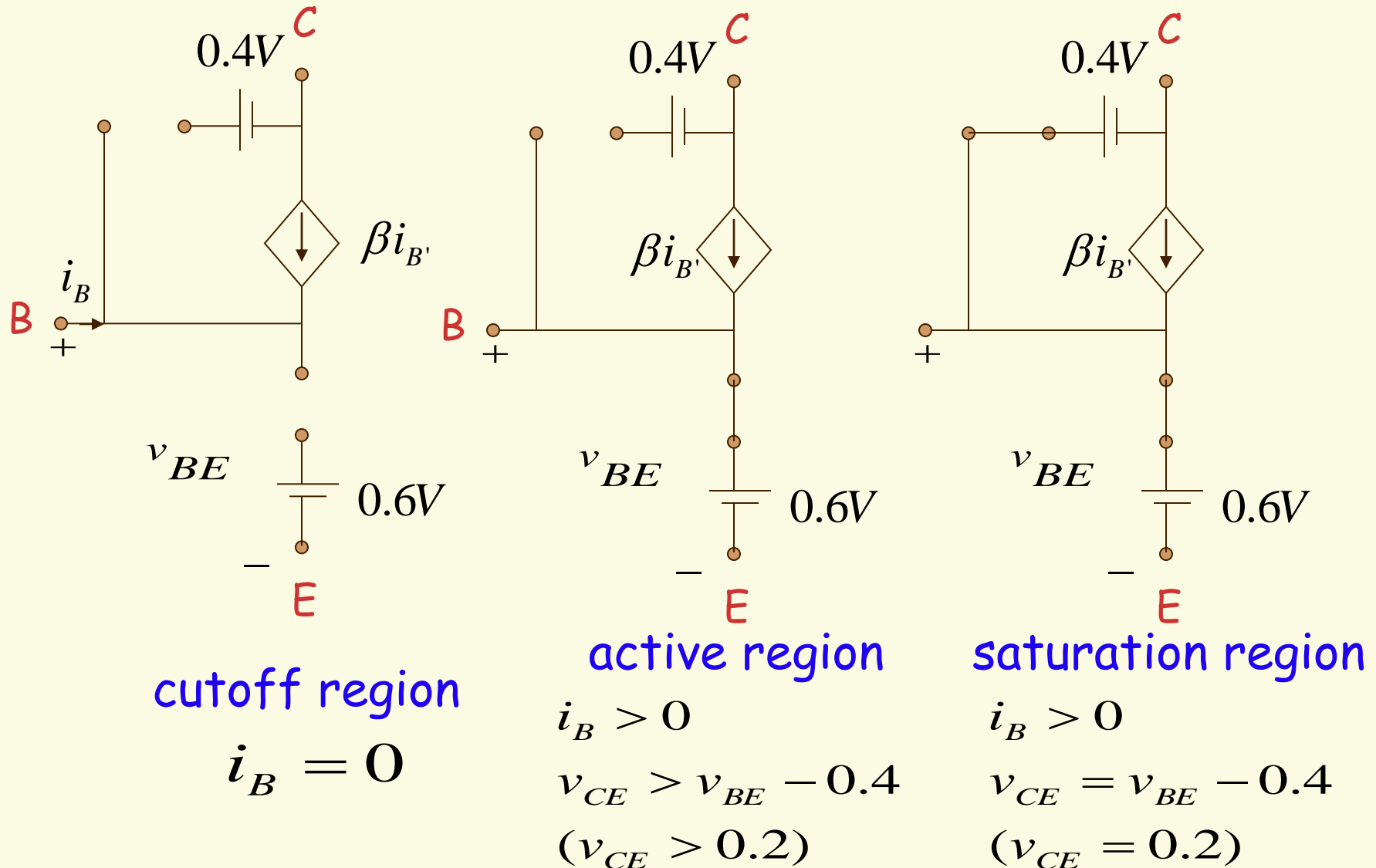
Active region: $V_{BE} = 0.6 \sim 0.7$, almost constant

BJT Model

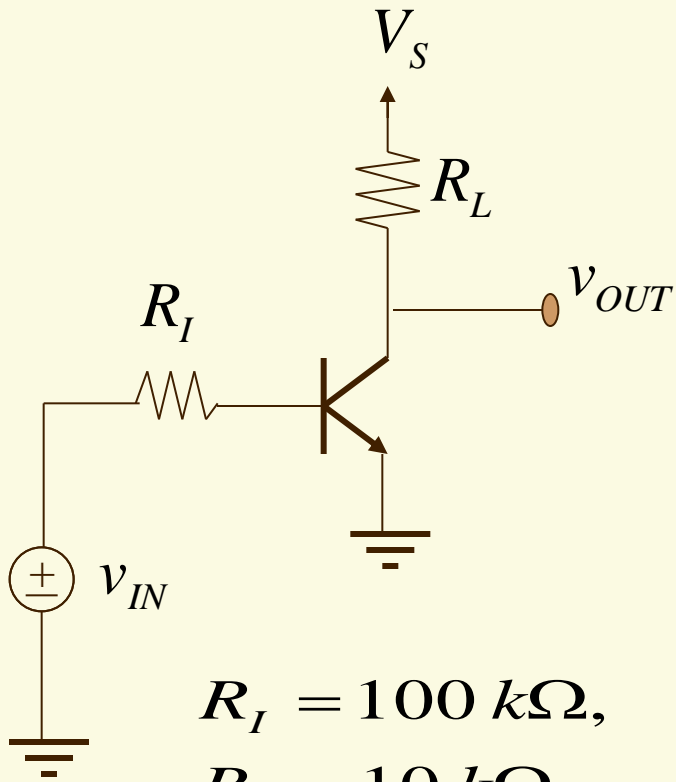


Piecewise-linear model

BJT Models in various regions of operation



Example 7.15 BJT Amplifier



$$v_O = ?$$

$$v_{IN} = 1, 1.1, 1.2 \text{ V}$$

$$R_I = 100 \text{ k}\Omega,$$

$$R_L = 10 \text{ k}\Omega,$$

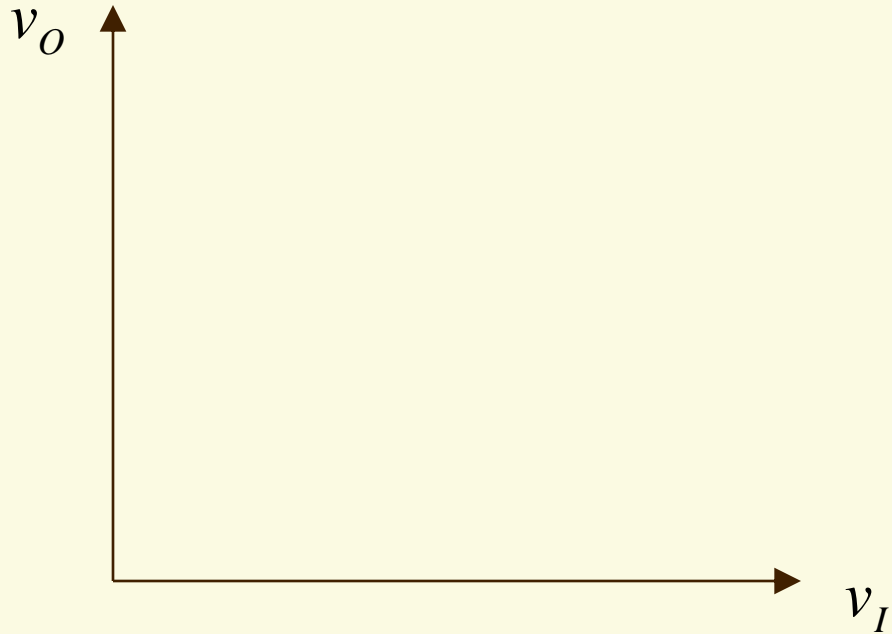
$$\beta = 100,$$

$$V_S = 10 \text{ V}$$

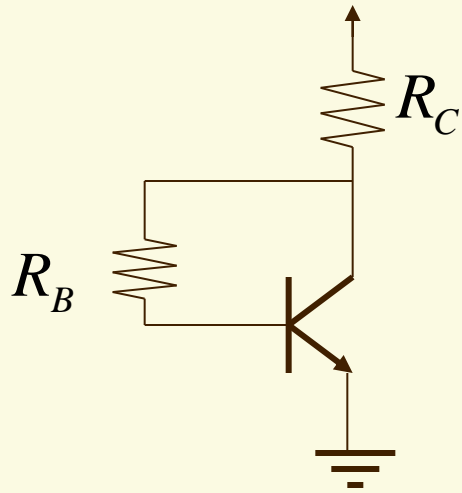
Large Signal Analysis

1. Relationship between v_O and v_{IN}
2. What is the range of valid input values for active region operation of the BJT? What is the corresponding range of output values?

Voltage characteristics of BJT Amplifier



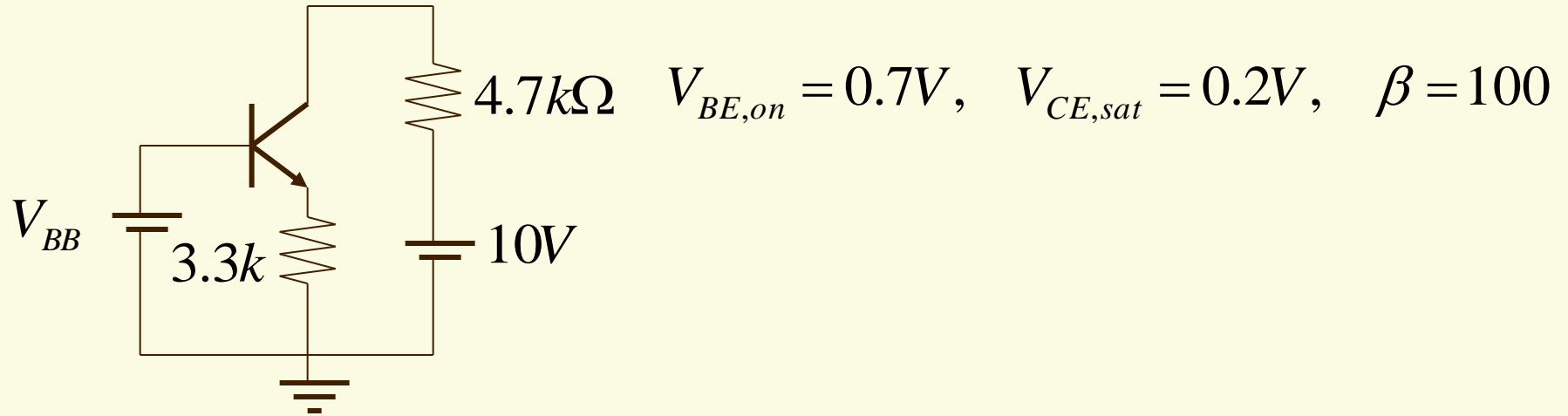
Exercise 1



$$R_C = 4k, R_B = 100k\Omega$$

$$V_{CC} = 15V, V_D = 0.7V, \beta = 99$$

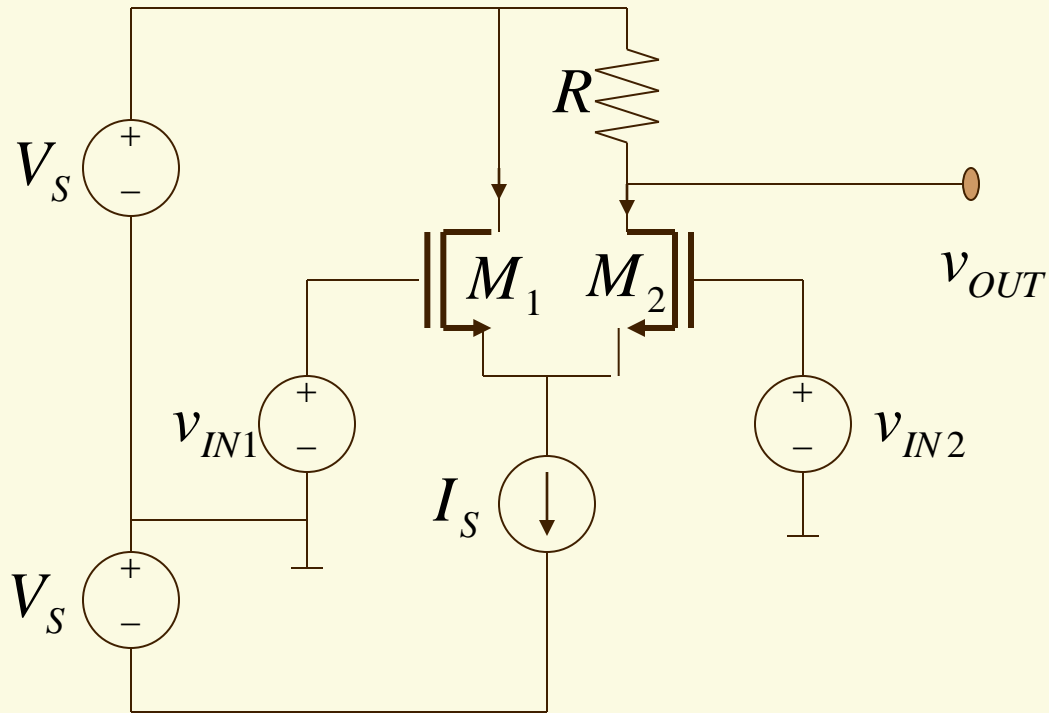
Exercise 2: compute the bias condition



(1) $V_{BB} = 4.0V$

(2) $V_{BB} = 6.0V$

Example 7.19 Differential Amplifier



Conclusion

- 📄 MOSFET Amplifier
- 📄 MOSFET and SCS Model
- 📄 Large Signal Analysis
- 📄 BJT Amplifier
- 📄 Differential Amplifier